

# **Investigation of stacking mismatched domain Structure of the $\gamma$ - $\text{Al}_2\text{O}_3$ formed on c-plane sapphire substrate by solid phase epitaxy**

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# Outline

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## Introduction

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- Growth of GaN on Sapphire ( $\alpha$ -Al<sub>2</sub>O<sub>3</sub>) nano-membrane
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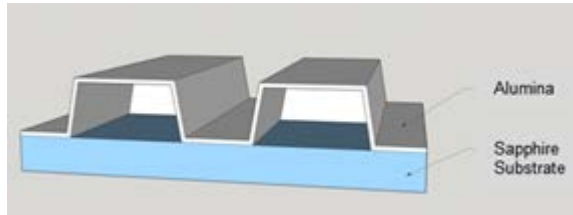
## Experiments & Analysis

- Fabrication of  $\alpha$ -Al<sub>2</sub>O<sub>3</sub> /  $\gamma$ -Al<sub>2</sub>O<sub>3</sub> nano-membrane
  - TEM analysis on the SPE  $\gamma$ -Al<sub>2</sub>O<sub>3</sub> layer
  - DFT calculation
- 

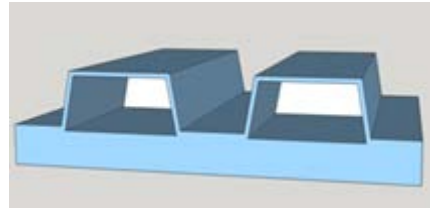


# Growth of GaN on sapphire membrane

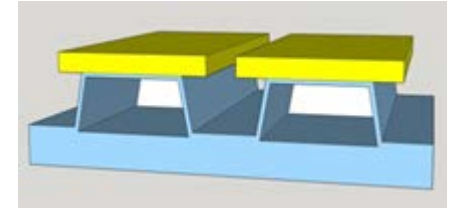
## ❖ Growth of GaN on an ultra thin compliant sapphire membrane



ALD + PR removal

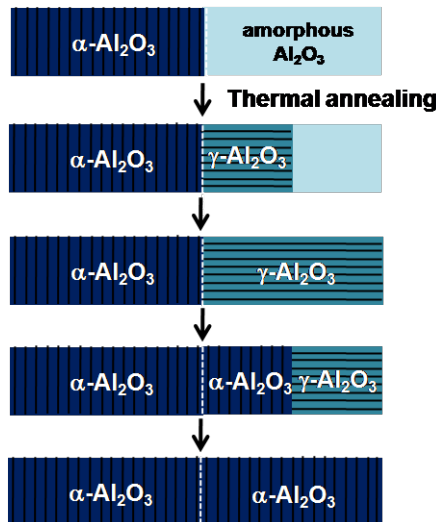


Solid phase epitaxy

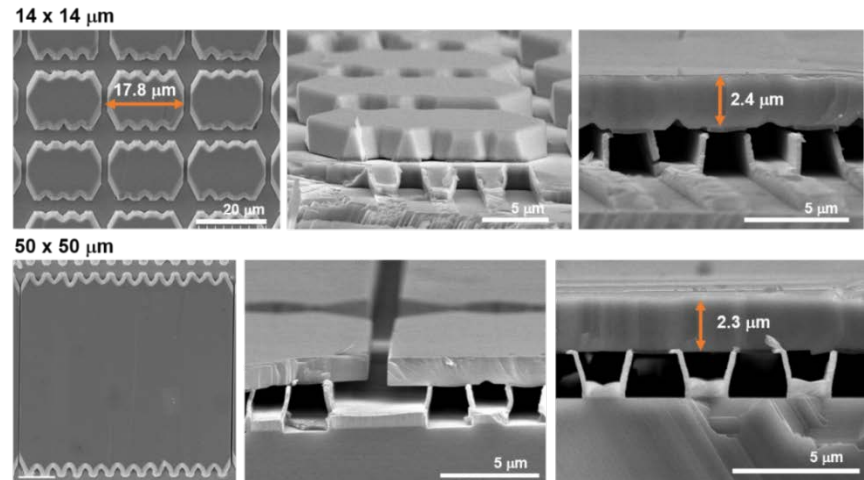


GaN growth

### ➤ Solid phase epitaxy of alumina

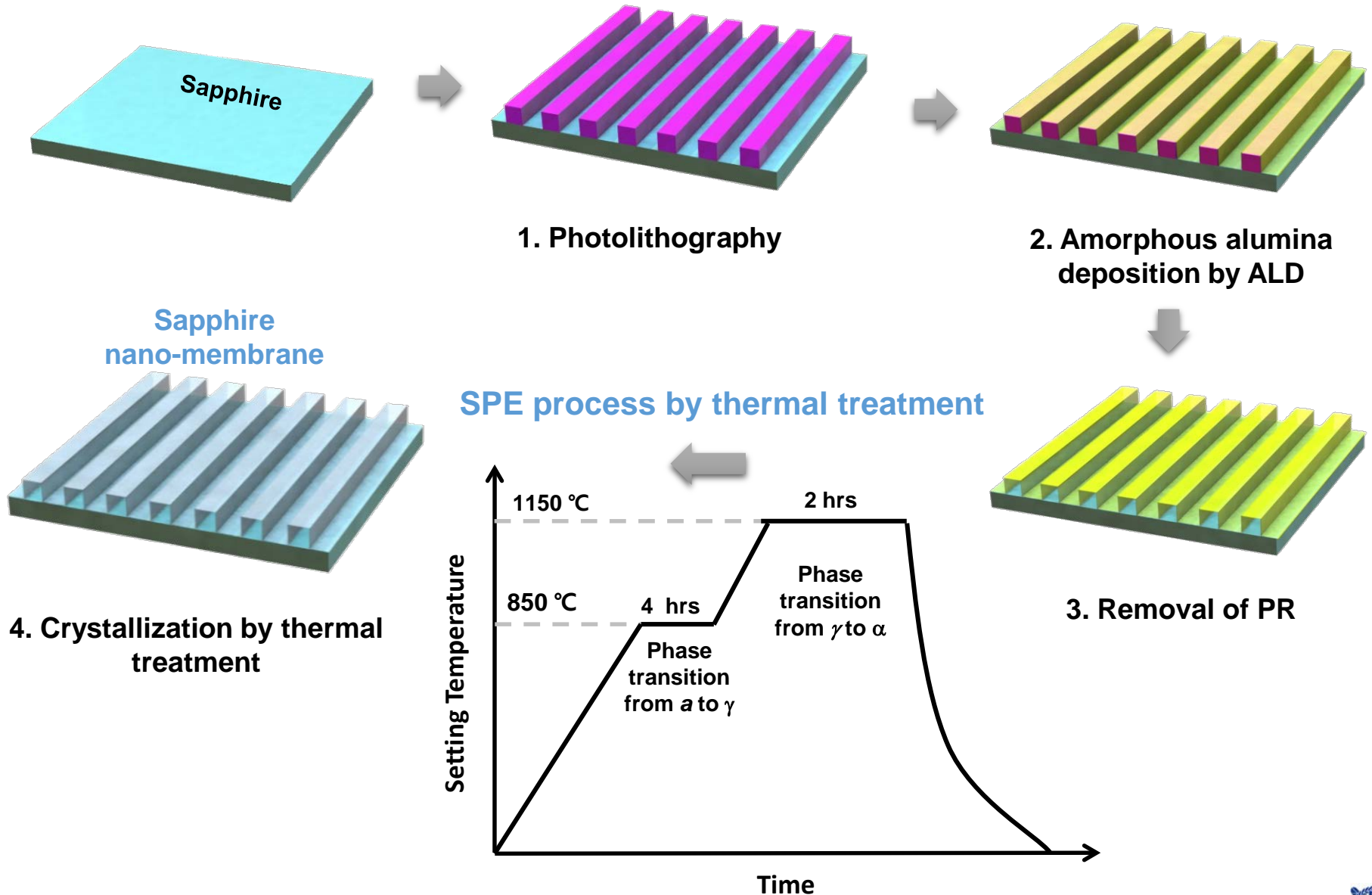


### ➤ Micro chip-sized GaN layer



- Understanding the SPE process of the 3D alumina membrane structure is needed.
- To obtain high quality  $\alpha\text{-Al}_2\text{O}_3$ , fundamental study on the intermediate  $\gamma\text{-Al}_2\text{O}_3$  need to be carried out.

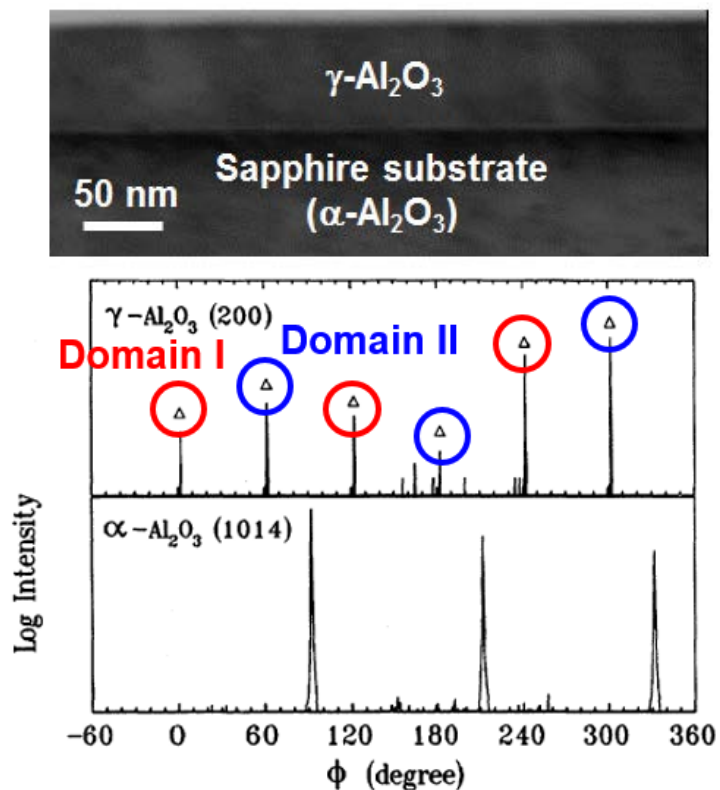
# Experimental details



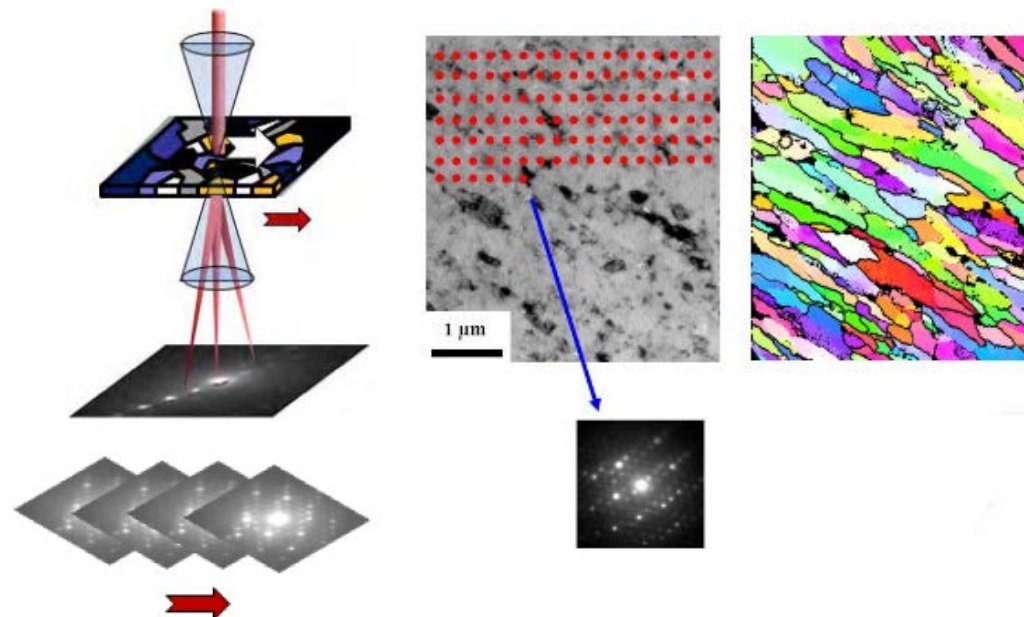
# Analysis of $\gamma\text{-Al}_2\text{O}_3/\alpha\text{-Al}_2\text{O}_3$ interface

- $\gamma\text{-Al}_2\text{O}_3/\alpha\text{-Al}_2\text{O}_3$  interface\_ 850 °C 1 hr

## <XRD phi scan>



## <TEM phase analysis>



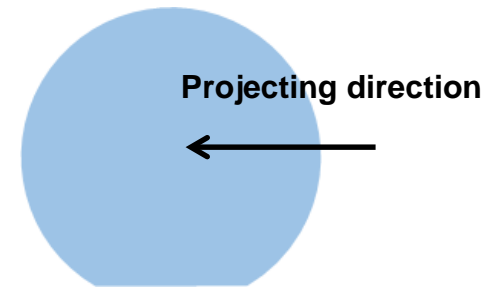
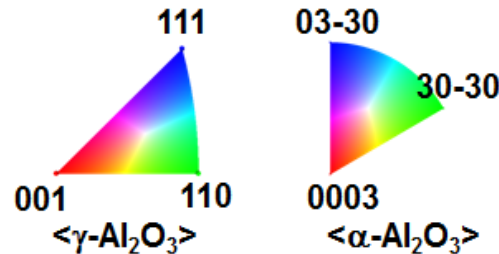
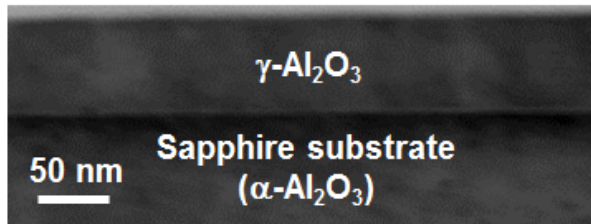
[www.nanomegas.com](http://www.nanomegas.com)

- From the XRD phi scan,  $\gamma\text{-Al}_2\text{O}_3$  has two kinds of domain.
- The phase/orientation mapping was conducted for the alumina layer annealed at 850 °C for 1 hr.

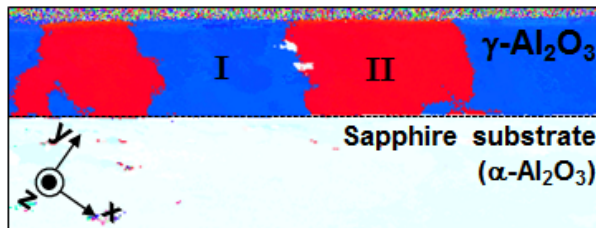
# Phase/orientation mapping of $\gamma\text{-Al}_2\text{O}_3$ layer

Projecting direction:  $\langle 10\text{-}10 \rangle_\alpha // \langle 110 \rangle_\gamma$

<Virtual bright field image>



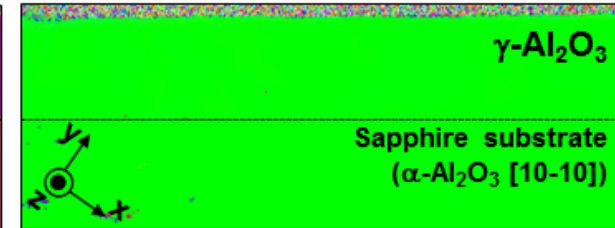
<Phase/orientation map>



x-axis ( $[-221]_{\gamma, I} + [00\text{-}1]_{\gamma, II}$ )



y-axis ( $[1\text{-}14]_{\gamma, I} + [1\text{-}10]_{\gamma, II}$ )

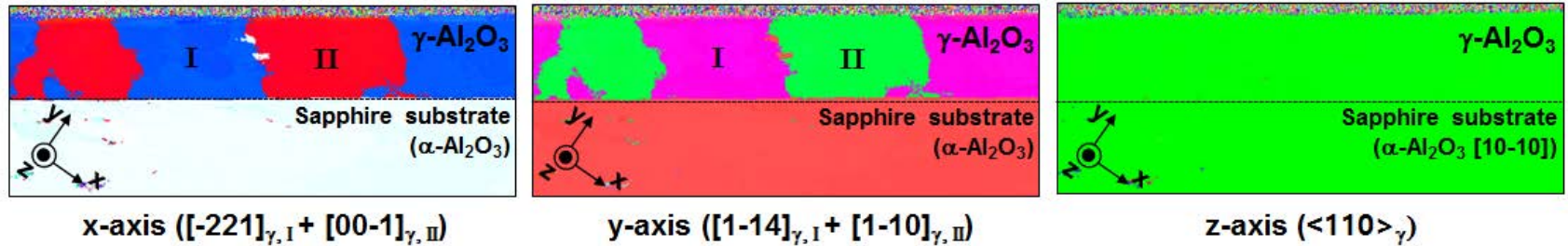


z-axis ( $\langle 110 \rangle_\gamma$ )

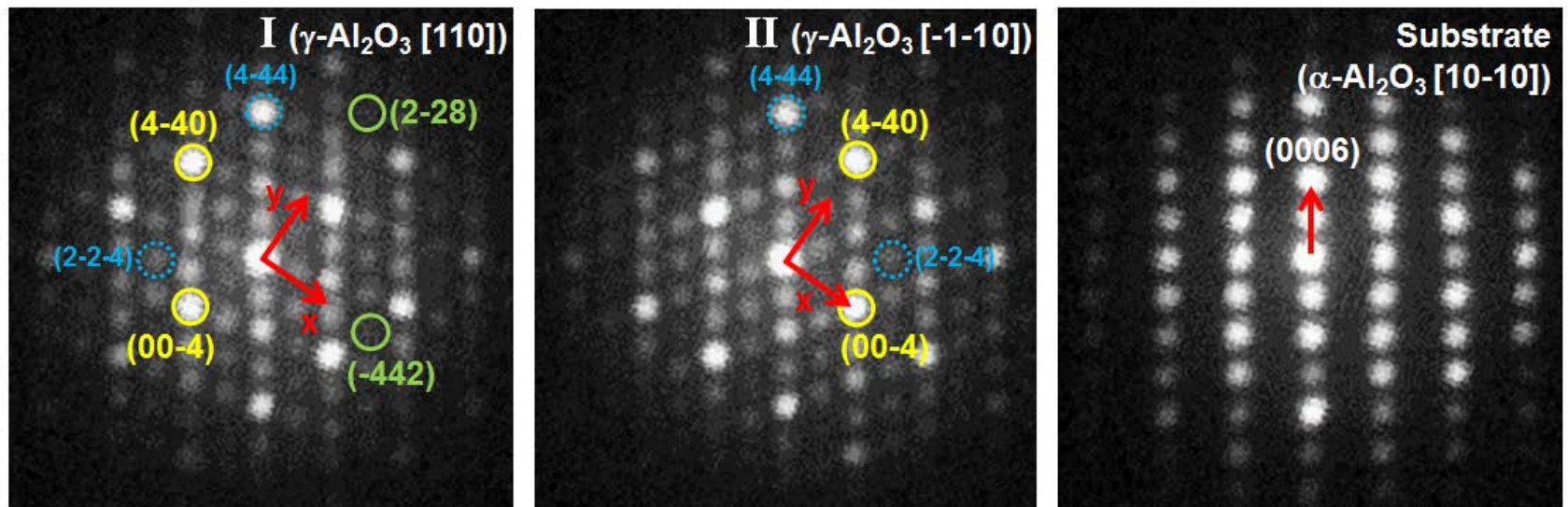
- Phase/orientation maps show that the  $\gamma\text{-Al}_2\text{O}_3$  layer consists of two kinds of domain.



# Phase/orientation mapping of $\gamma$ - $\text{Al}_2\text{O}_3$ layer



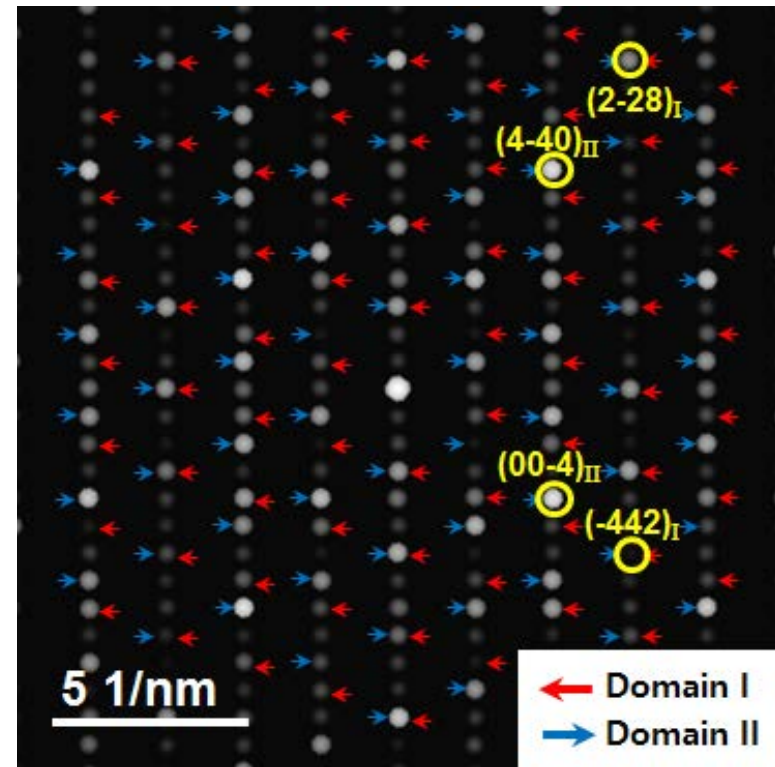
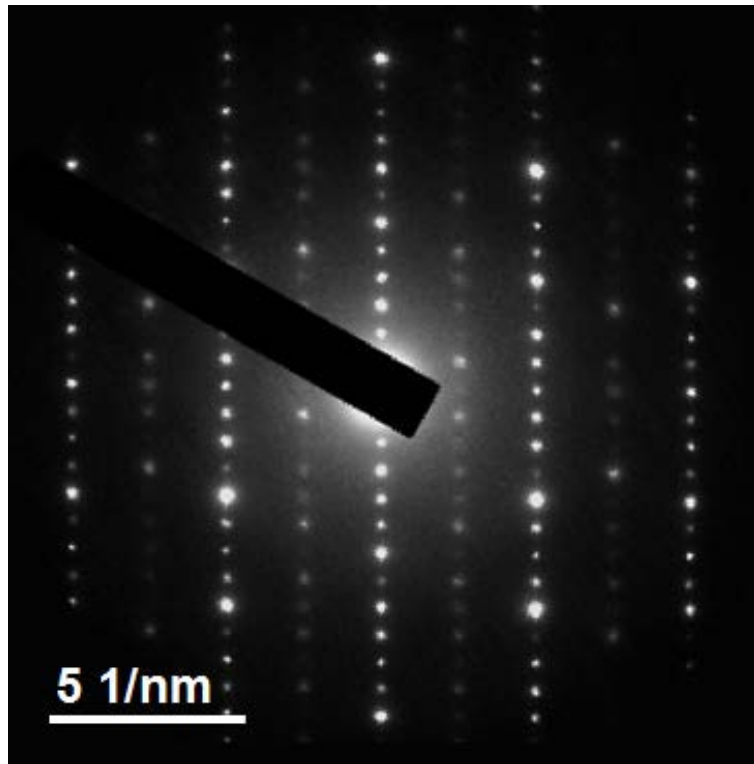
## <Nanobeam electron diffraction pattern>



- The two NPED patterns are in a symmetrical relationship with the virtual vertical line as the symmetry axis, which implies that Domains I and II form twin structure.

# Selected area electron diffraction pattern of $\gamma$ -Al<sub>2</sub>O<sub>3</sub> layer

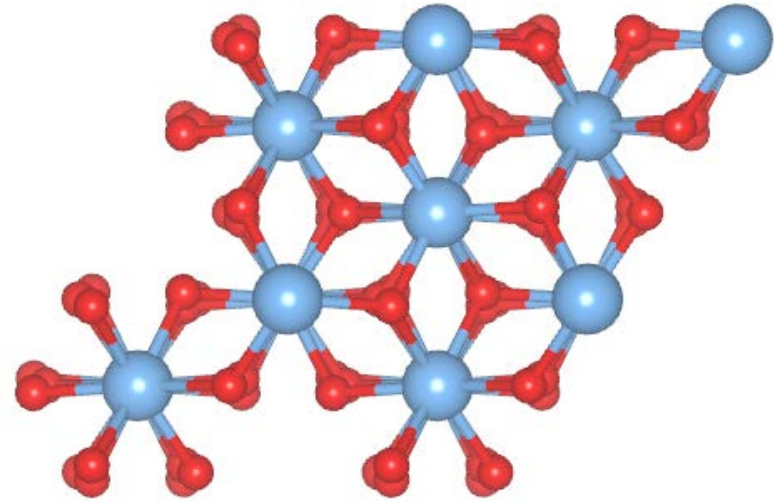
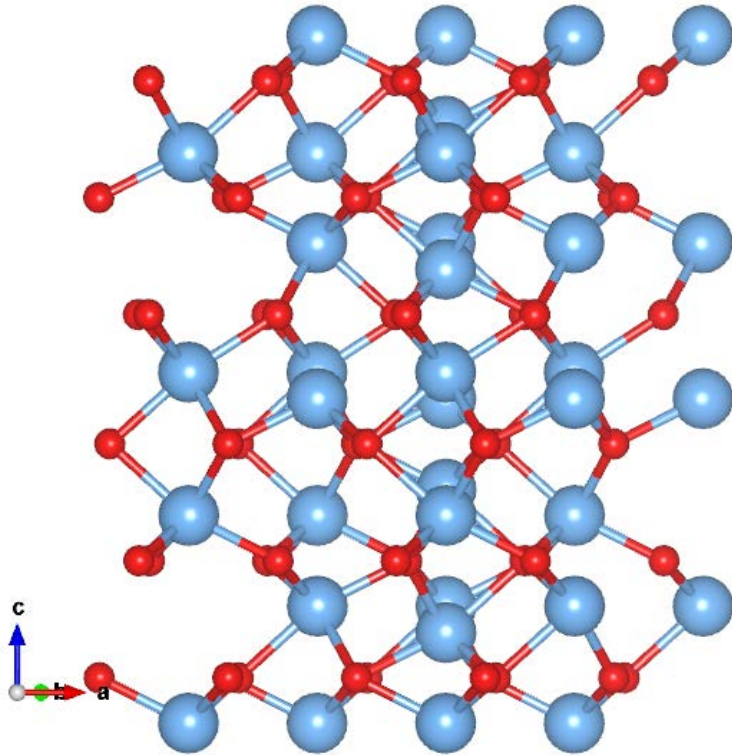
Zone axis:  $\langle 110 \rangle_\gamma$



- The simulated SAED patterns are consistent with the experimental SAED pattern.

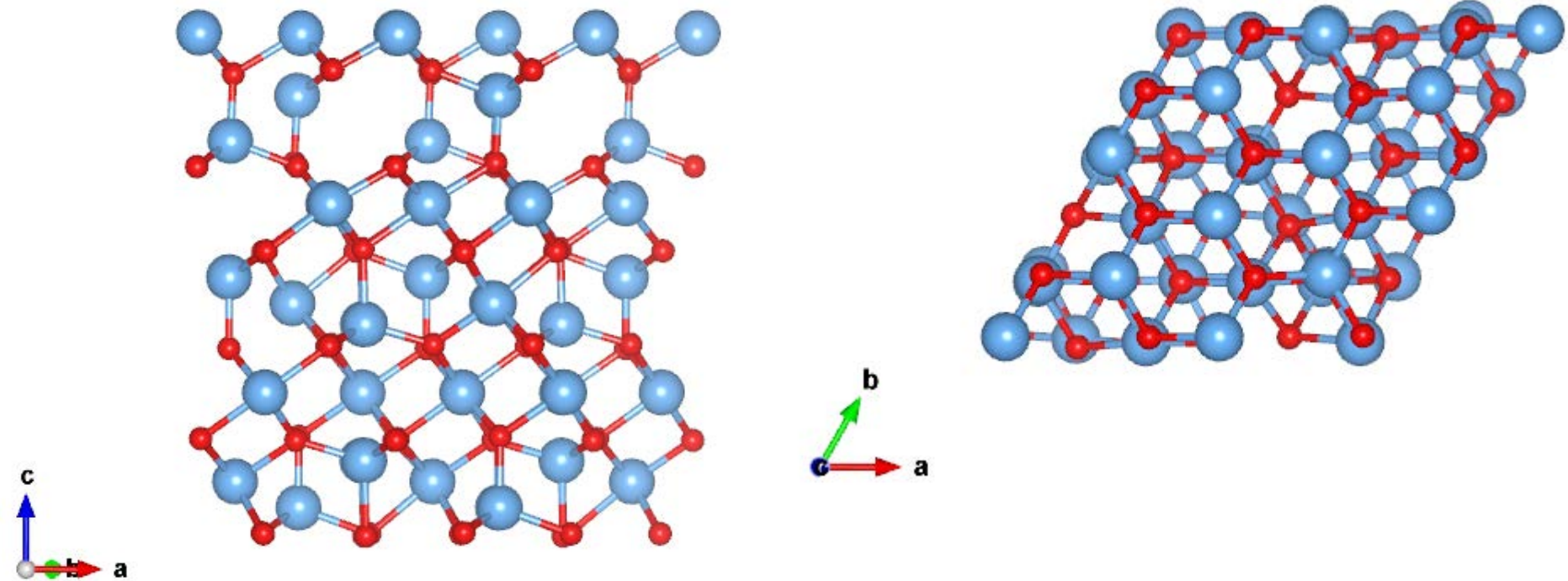


# Energetics of $\gamma$ -Al<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Al<sub>2</sub>O<sub>3</sub> interface-DFT



- $\alpha$ -Al<sub>2</sub>O<sub>3</sub> unit cell
- Structure of  $\alpha$ -Al<sub>2</sub>O<sub>3</sub> shown on [10-10], [1-210], [0001], respectively.

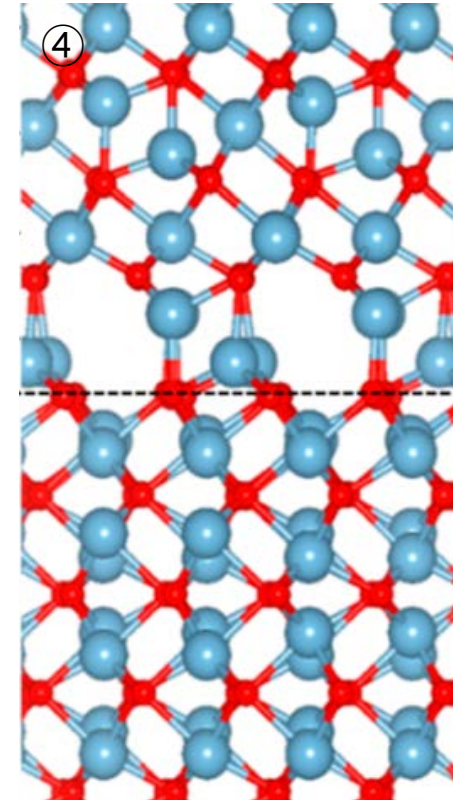
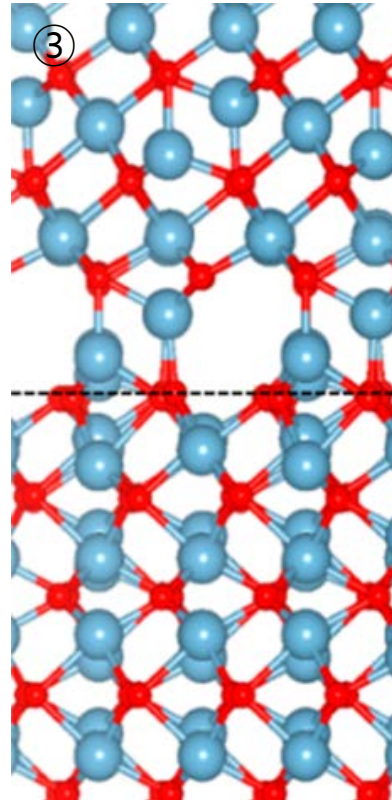
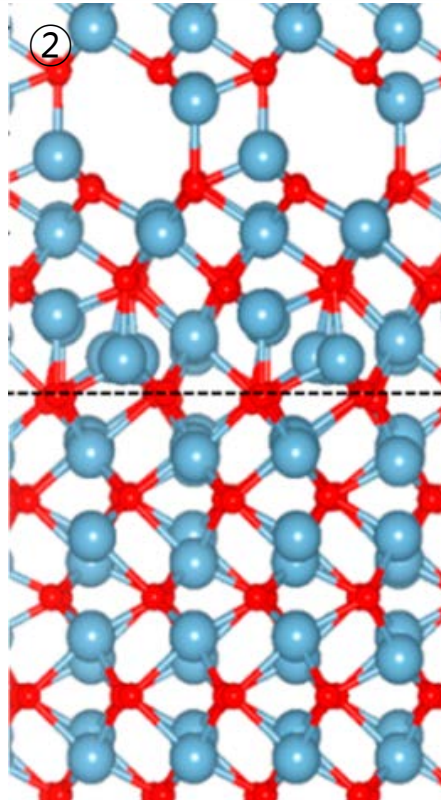
# Energetics of $\gamma$ -Al<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Al<sub>2</sub>O<sub>3</sub> interface-DFT



- $\gamma$ -Al<sub>2</sub>O<sub>3</sub> unit cell with [110], [-112], [1-11]
- Spinel-similar structure, but 8/3 cation vacancies must be introduced.

# Energetics of $\gamma$ -Al<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Al<sub>2</sub>O<sub>3</sub> interface-DFT

①



- For different heterostructure
- Bottom :  $\alpha$ -Al<sub>2</sub>O<sub>3</sub> with [10-10], [1-210], [0001] for a, b, c axis.
- Top :  $\gamma$ -Al<sub>2</sub>O<sub>3</sub> with [110], [-112], [1-11] for a, b, c axis(① and ③)  
 $\gamma$ -Al<sub>2</sub>O<sub>3</sub> with [-1-10], [1-1-2], [1-11] for a, b, c axis(② and ④)

# Energetics of $\gamma$ -Al<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Al<sub>2</sub>O<sub>3</sub> interface-DFT

Structure	Energy(relative, eV)
1	0
2	0.11
3	12.35
4	11.39

- Difference between ①, ③ and ②, ④ : position of Al vacancy
- Structure ③ and ④ : are not probable (energetically unfavored)
- Structure ① and ② : very small energy difference – both domains are probable in experiment



# Summary

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- ✓ Solid-phase crystallization of 3-D  $\text{Al}_2\text{O}_3$  membrane structure was investigated, showing the phase transformation sequence from amorphous to  $\gamma$ -(SPE & RNG) and then to  $\alpha$ -phase (SPE).
- ✓ The epitaxial  $\gamma$ - $\text{Al}_2\text{O}_3$  consisted of two stacking-mismatched domains, which can be distinguished at specific directions by XRD scan.
- ✓ The simulated SAED patterns are consistent with the experimental SAED pattern, which can confirm both domain I and II
- ✓ DFT calculation also confirms that both domain I and II are probable.





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**THANK YOU FOR LISTENING**

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